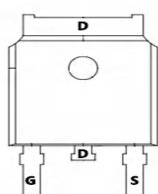


TM40P04D

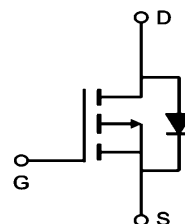
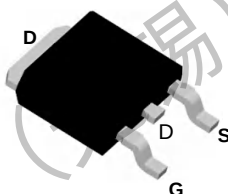
P-Channel Enhancement Mosfet

General Description • Low $R_{DS(ON)}$ • RoHS and Halogen-Free Compliant Applications • Load switch • PWM	General Features $V_{DS} = -40V$ $I_D = -40A$ $R_{DS(ON)} = 13m\Omega$ (typ.) @ $V_{GS} = -10V$ 100% UIS Tested 100% R_g Tested 
--	--

D:TO-252-3L



Marking: 40P04



Absolute Maximum Ratings ($T_C = 25^\circ C$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-40	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-26	A
I_{DM}	Pulsed Drain Current	-148	A
EAS	Single Pulse Avalanche Energy	57.8	mJ
$P_D @ T_C = 25^\circ C$	Total Power Dissipation	40.3	W
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case	---	6.6	$^\circ C/W$

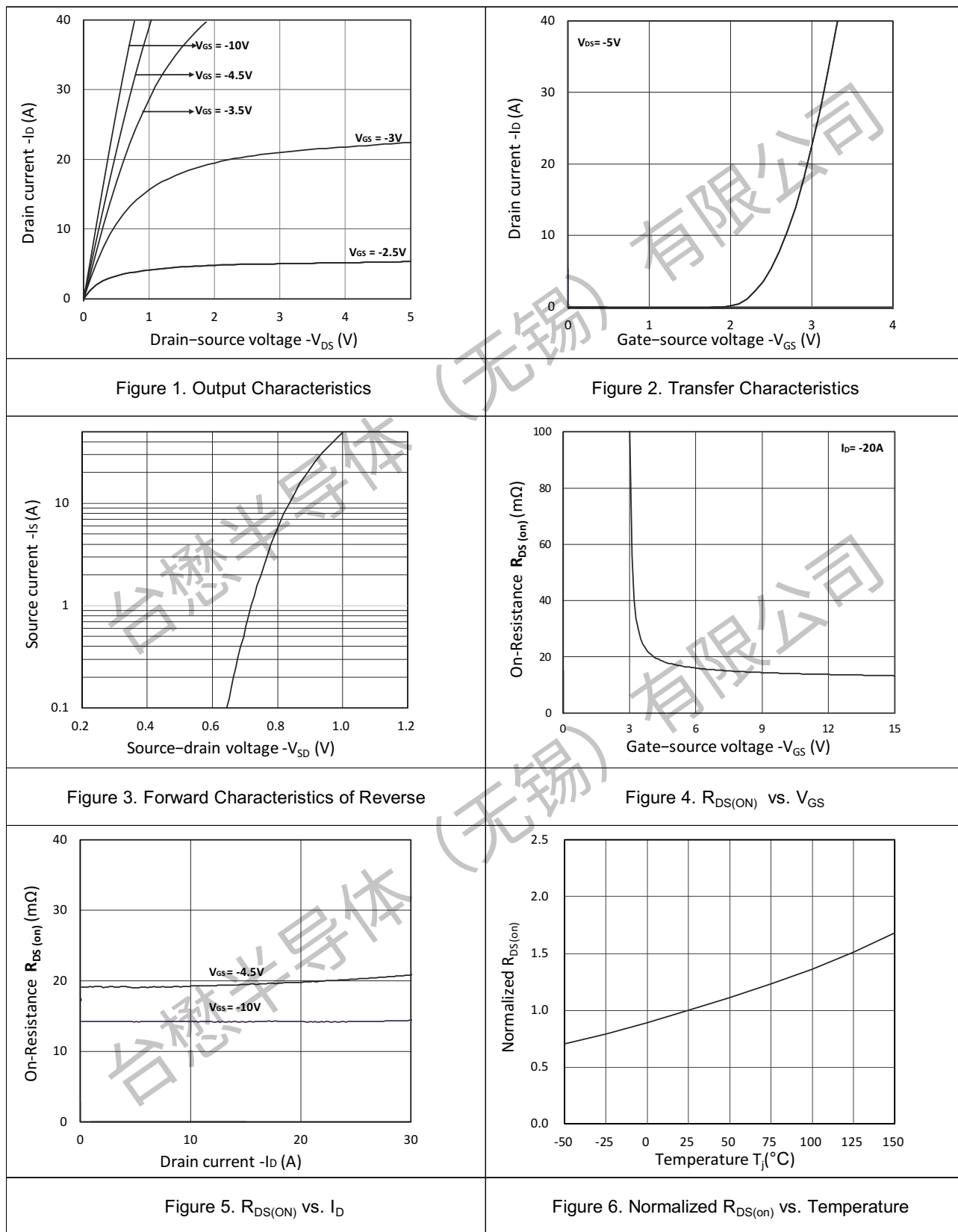
TM40P04D
P-Channel Enhancement Mosfet
Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics							
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-40	-	-	V
Gate-body Leakage current		I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	± 100	nA
Zero Gate Voltage Drain Current	$T_J=25^{\circ}C$	I_{DSS}	$V_{DS} = -40V, V_{GS} = 0V$	-	-	-1	μA
	$T_J=100^{\circ}C$			-	-	-100	
Gate-Threshold Voltage		$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.4	-1.75	-2.0	V
Drain-Source On-Resistance ⁴		$R_{DS(on)}$	$V_{GS} = -10V, I_D = -20A$	-	13	19	mΩ
			$V_{GS} = -4.5V, I_D = -15A$	-	18	25	
Forward Transconductance ⁴		g_{fs}	$V_{DS} = -10V, I_D = -20A$	-	44	-	S
Dynamic Characteristics ⁵							
Input Capacitance		C_{iss}	$V_{DS} = -20V, V_{GS} = 0V, f = 1MHz$	-	1500	-	pF
Output Capacitance		C_{oss}		-	235	-	
Reverse Transfer Capacitance		C_{rss}		-	180	-	
Gate Resistance		R_g	$f = 1MHz$	-	5	-	Ω
Switching Characteristics ⁵							
Total Gate Charge		Q_g	$V_{GS} = -10V, V_{DS} = -20V, I_D = -20A$	-	35	-	nC
Gate-Source Charge		Q_{gs}		-	5.5	-	
Gate-Drain Charge		Q_{gd}		-	8	-	
Turn-On Delay Time		$t_{d(on)}$	$V_{GS} = -10V, V_{DD} = -20V, R_G = 3\Omega, I_D = -20A$	-	14.5	-	ns
Rise Time		t_r		-	20.2	-	
Turn-Off Delay Time		$t_{d(off)}$		-	32	-	
Fall Time		t_f		-	10	-	
Drain-Source Body Diode Characteristics							
Diode Forward Voltage ⁴		V_{SD}	$I_S = -20A, V_{GS} = 0V$	-	-	-1.2	V
Continuous Source Current	$T_C=25^{\circ}C$	I_S	-	-	-	-40	A

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Typical Characteristics



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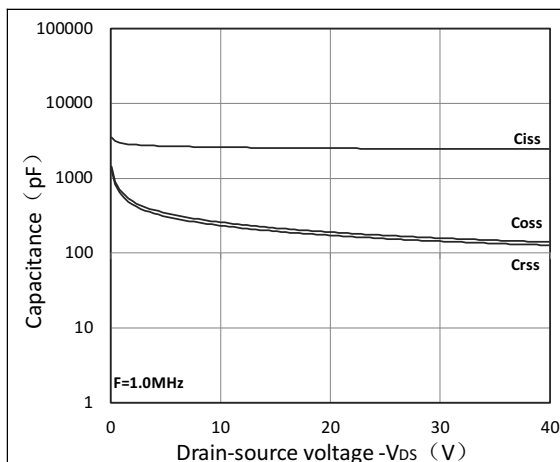


Figure 7. Capacitance Characteristics

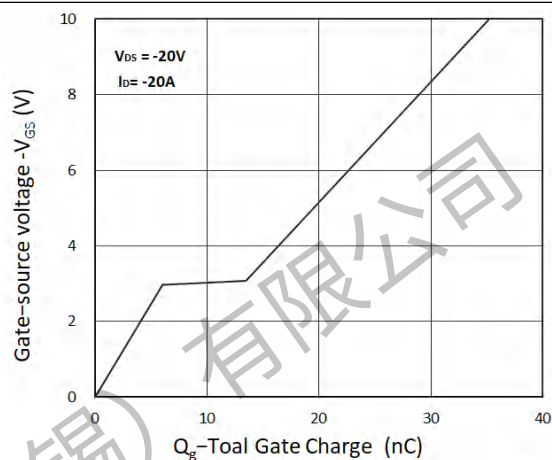


Figure 8. Gate Charge Characteristics

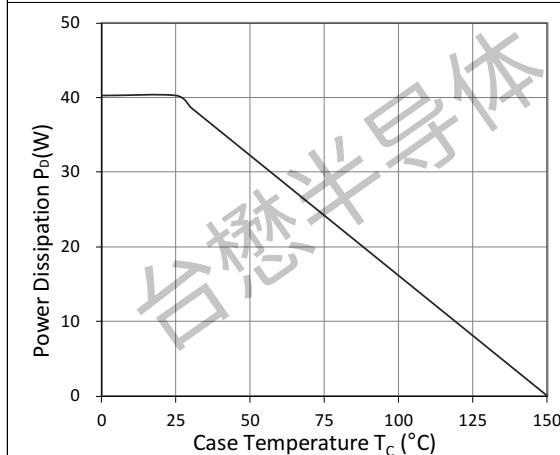


Figure 9. Power Dissipation

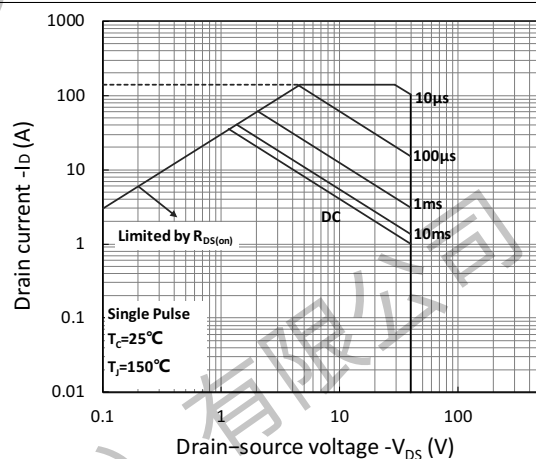


Figure 10. Safe Operating Area

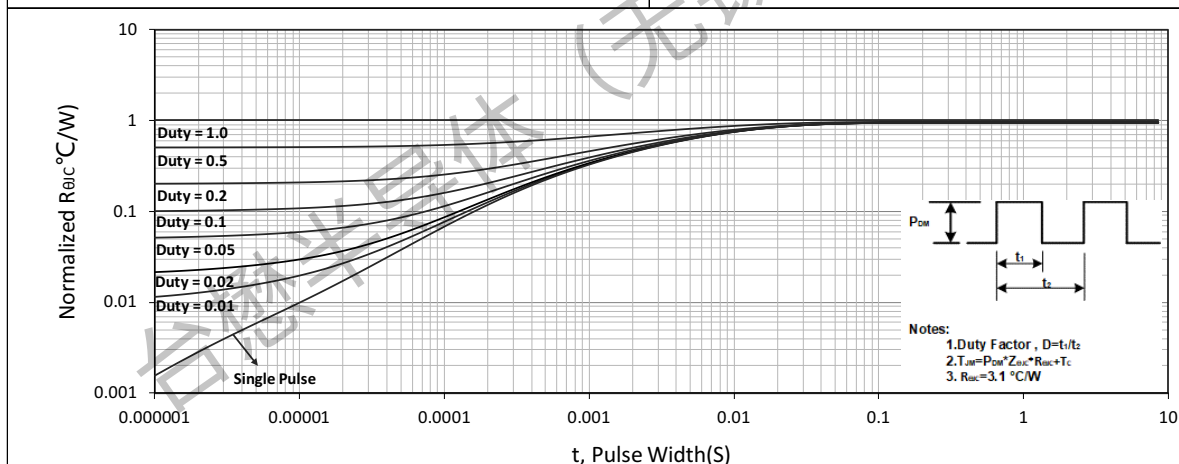
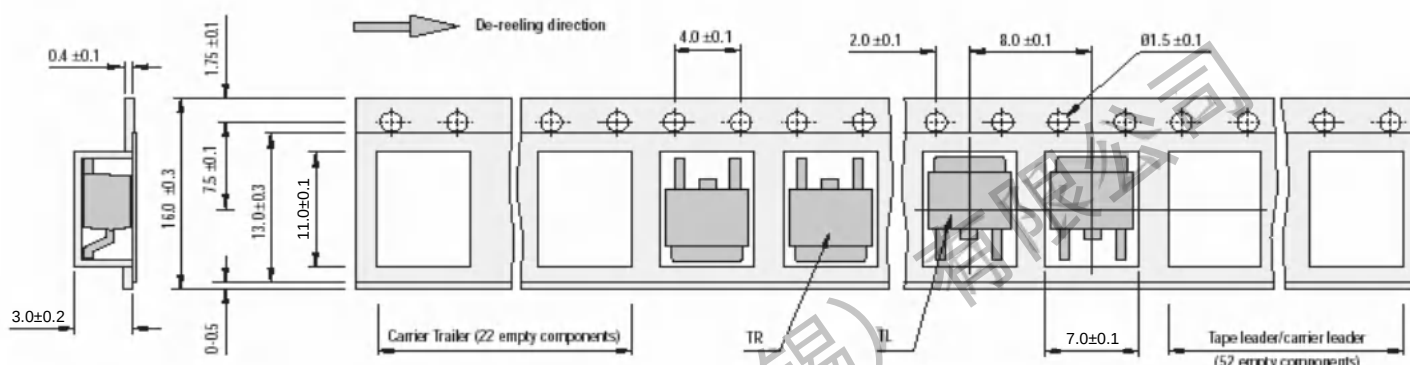


Figure 11. Normalized Maximum Transient Thermal Impedance

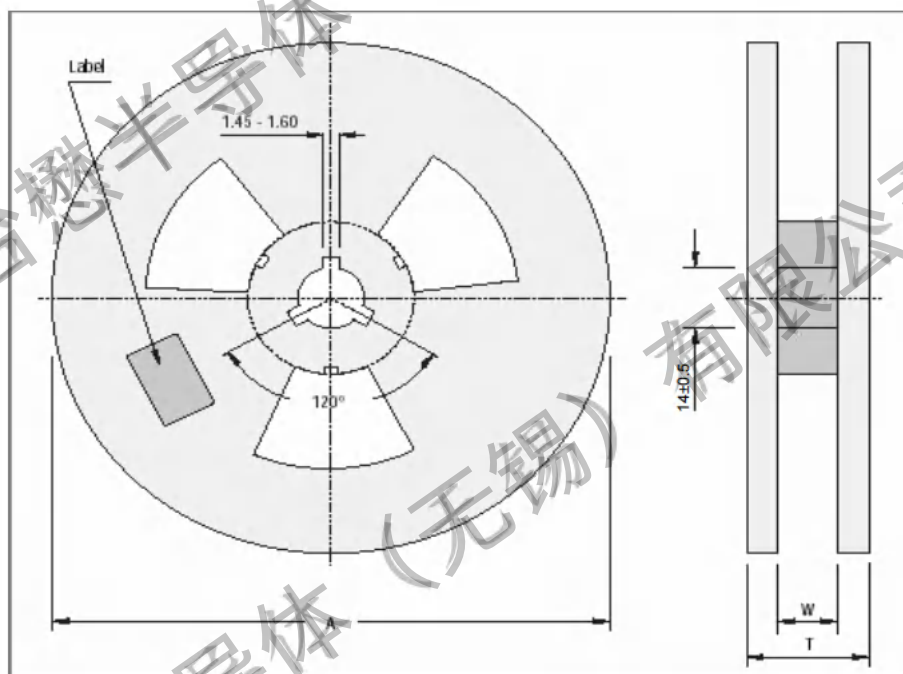
TM40P04D

P-Channel Enhancement Mosfet

TO-252-3L Embossed Carrier Tape



TO-252-3L Reel



All Dimensions are in mm.

Reel Specifications				
Package	Tape Width	Reel Dia. A - Max	Inside Thickness W	Reel Thickness T - max
TO-252-3L	16	330	18.0 ± 1.5	20

Packaging Information

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
2,500 pcs	13 inch	5,000 pcs	355×370×50	25,000 pcs	380×275×380	

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Revision history:

Date	Rev	Description	Page
2023.06.01	23.06	Original	